Ordering number : ENA1498

SANYO Semiconductors

DATA SHEET

N-Channel Silicon MOSFET

2SK4179GS — General-Purpose Switching Device Applications

Features

- Low ON-resistance.
- Motor drive.
- Avalanche resistance guarantee.
- 10V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		75	V
Gate-to-Source Voltage	V_{GSS}		±20	V
Drain Current (DC)	I_D		80	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	320	A
Allowable Power Dissipation	P_D		1.75	W
		Tc=25°C	70	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C
Avalanche Energy (Single Pulse) *1	E_{AS}		100	mJ
Avalanche Current *2	I_{AV}		48	A

Note :*1 V_{DD}=30V, L=50μH, I_{AV}=48A
*2 L≤50μH, Single pulse

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0V	75			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=75V, V_{GS}=0V			1	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±16V, V_{DS}=0V			±10	μA

Marking : K4179

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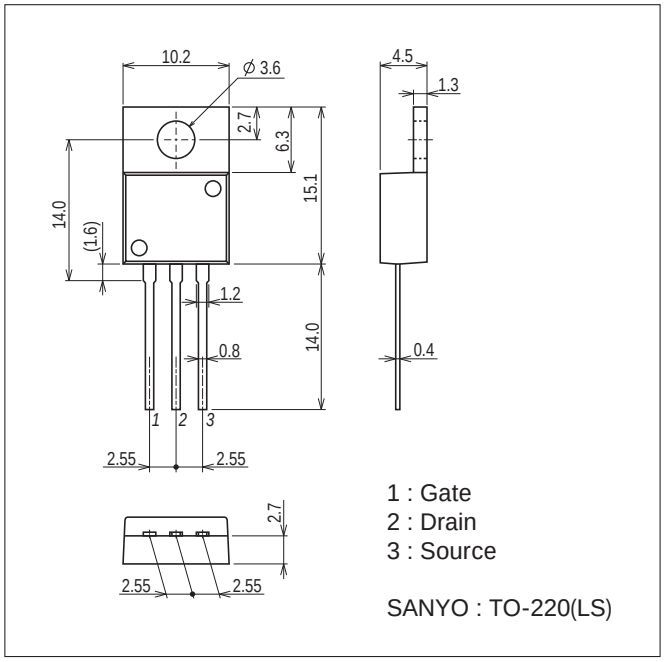
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Cutoff Voltage	V_{GS}(off)	V_{DS}=10V, I_D=1mA	2		4	V
Forward Transfer Admittance	| yfs |	V_{DS}=10V, I_D=40A		35		S
Static Drain-to-Source On-State Resistance	R_{DS}(on)	I_D=40A, V_{GS}=10V		10.5	13.7	mΩ
Input Capacitance	Ciss	V_{DS}=20V, f=1MHz		5400		pF
Output Capacitance	Coss	V_{DS}=20V, f=1MHz		480		pF
Reverse Transfer Capacitance	Crss	V_{DS}=20V, f=1MHz		350		pF
Turn-ON Delay Time	t_d(on)	See specified Test Circuit.		62		ns
Rise Time	t_r	See specified Test Circuit.		335		ns
Turn-OFF Delay Time	t_d(off)	See specified Test Circuit.		220		ns
Fall Time	t_f	See specified Test Circuit.		160		ns
Total Gate Charge	Qg	V_{DS}=30V, V_{GS}=10V, I_D=80A		100		nC
Gate-to-Source Charge	Qgs	V_{DS}=30V, V_{GS}=10V, I_D=80A		30		nC
Gate-to-Drain “Miller” Charge	Qgd	V_{DS}=30V, V_{GS}=10V, I_D=80A		28		nC
Diode Forward Voltage	V_{SD}	I_S=80A, V_{GS}=0V		1.07	1.5	V

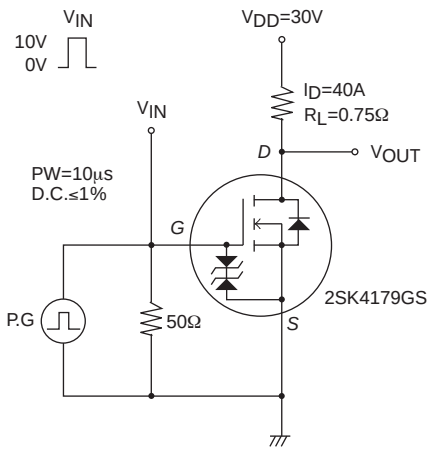
Package Dimensions

unit : mm (typ)

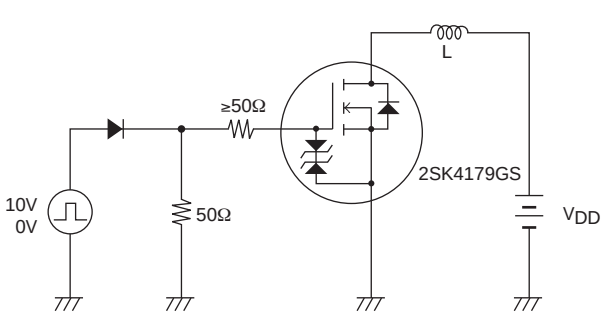
7530-001

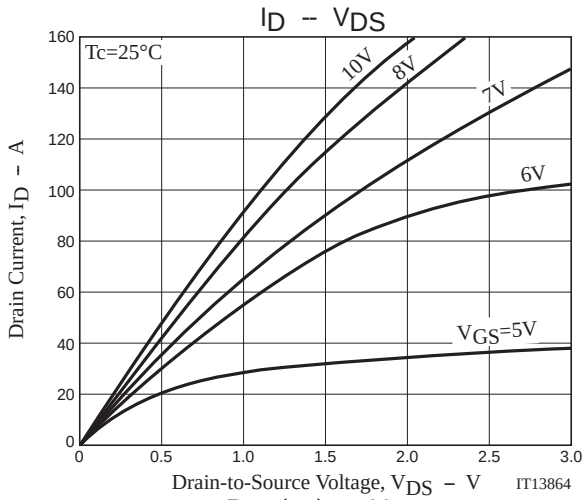


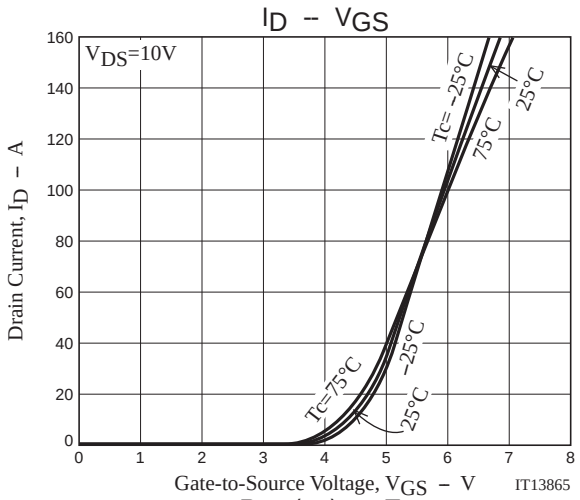
Switching Time Test Circuit

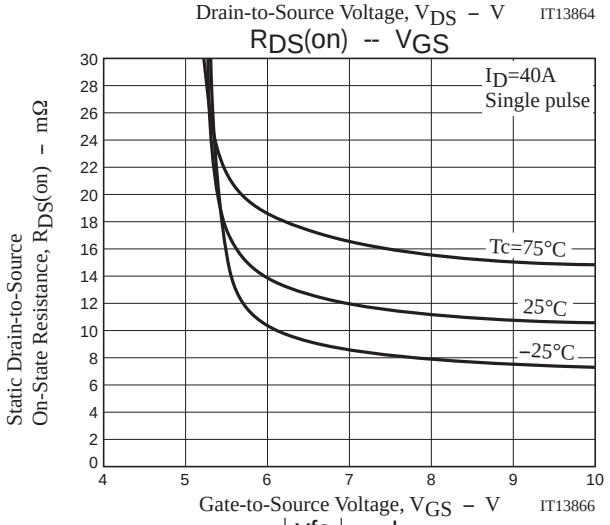


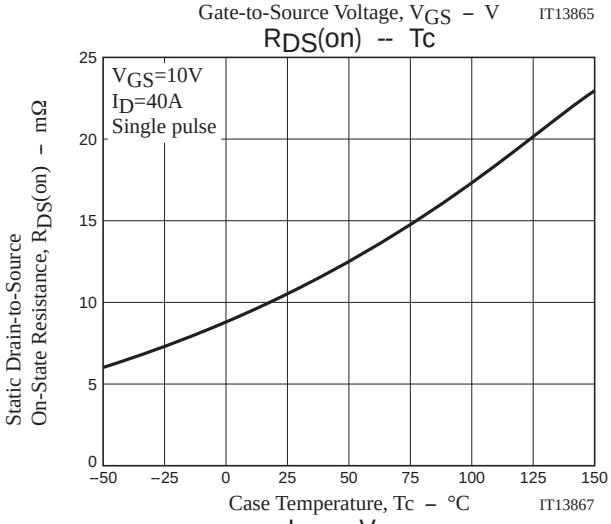
Avalanche Resistance Test Circuit

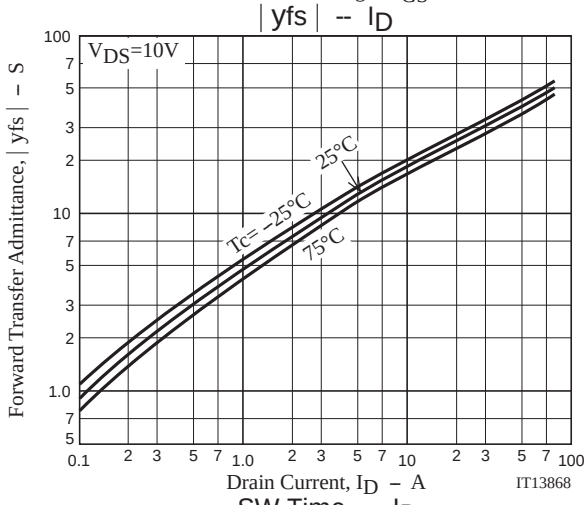


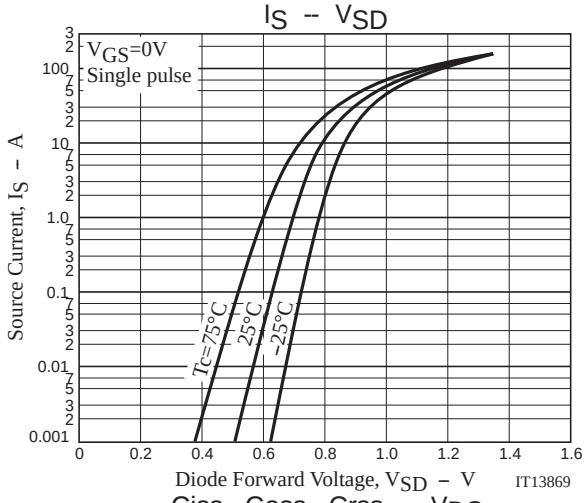

ID -- VDS
Tc=25°C
10V
8V
7V
6V
VGS=5V
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT13864

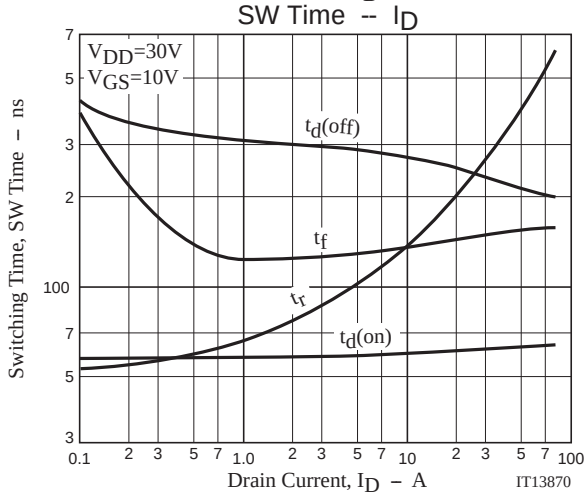

ID -- VGS
VDS=10V
Tc= –25°C
25°C
75°C
Tc=75°C
–25°C
25°C
Drain Current, ID – A
Gate-to-Source Voltage, VGS – V
IT13865

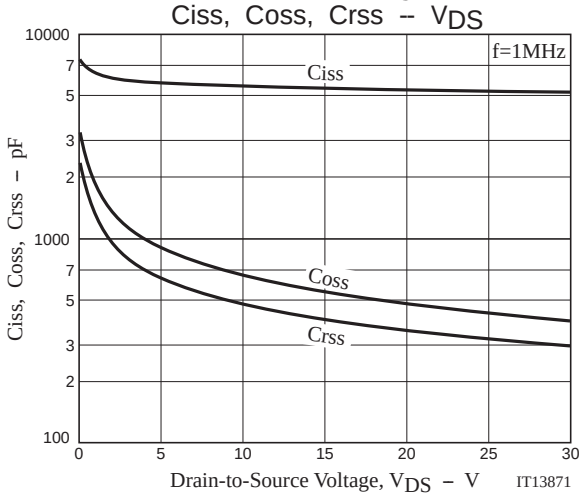

RDS(on) -- VGS
ID=40A
Single pulse
Tc=75°C
25°C
–25°C
Static Drain-to-Source
On-State Resistance, RDS(on) – mΩ
Gate-to-Source Voltage, VGS – V
IT13866

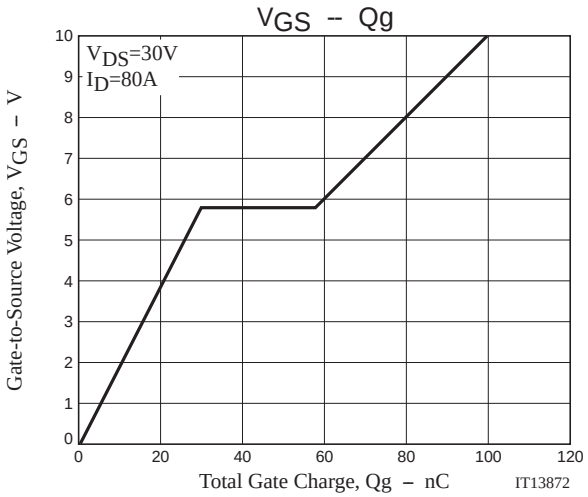

RDS(on) -- Tc
VGS=10V
ID=40A
Single pulse
Static Drain-to-Source
On-State Resistance, RDS(on) – mΩ
Case Temperature, Tc – °C
IT13867

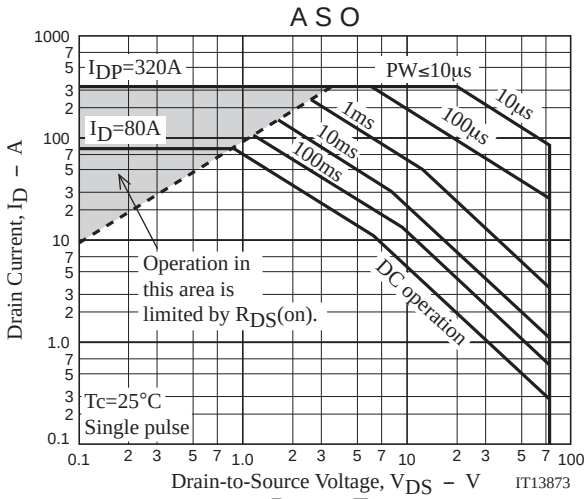

| yfs | -- ID
VDS=10V
25°C
Tc= –25°C
75°C
Forward Transfer Admittance, | yfs | – S
Drain Current, ID – A
IT13868

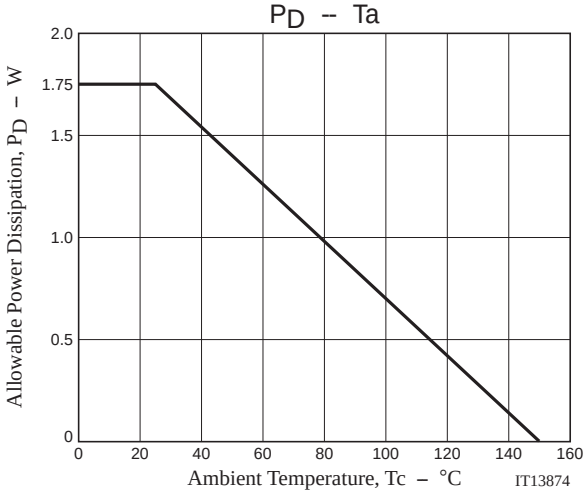

IS -- VSD
VGS=0V
Single pulse
Tc=75°C
25°C
–25°C
Source Current, IS – A
Diode Forward Voltage, VSD – V
IT13869

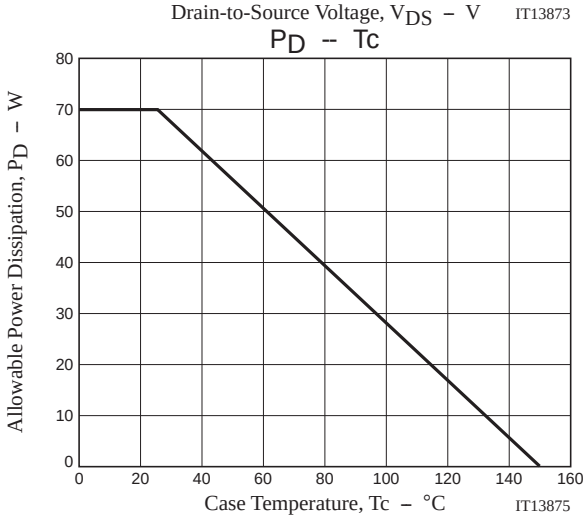

SW Time -- ID
VDD=30V
VGS=10V
td(off)
tf
tr
td(on)
Switching Time, SW Time – ns
Drain Current, ID – A
IT13870

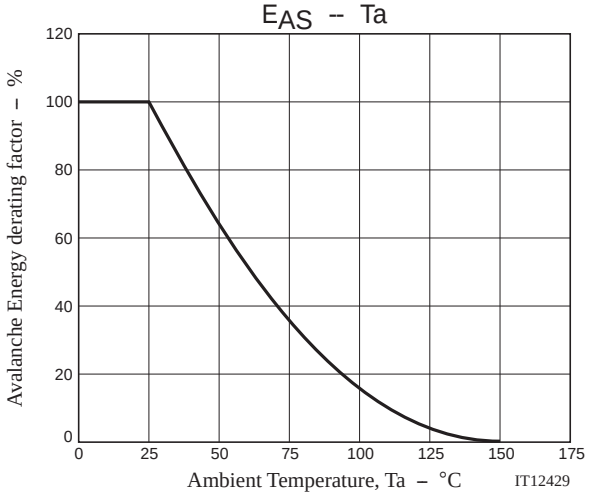

Ciss, Coss, Crss -- VDS
f=1MHz
Ciss
Coss
Crss
Ciss, Coss, Crss – pF
Drain-to-Source Voltage, VDS – V
IT13871


VGS – Qg
VDS=30V
ID=80A
Gate-to-Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT13872


A S O
IDP=320A
PW≤10μs
ID=80A
1ms
10μs
100μs
10ms
100ms
DC operation
Operation in this area is limited by RDS(on).
Tc=25°C
Single pulse
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT13873


PD – Ta
Allowable Power Dissipation, PD – W
Ambient Temperature, Tc – °C
IT13874


PD – Tc
Allowable Power Dissipation, PD – W
Case Temperature, Tc – °C
IT13875


EAS – Ta
Avalanche Energy derating factor – %
Ambient Temperature, Ta – °C
IT12429

Note on usage : Since the 2SK4179GS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

This catalog provides information as of June, 2009. Specifications and information herein are subject to change without notice.